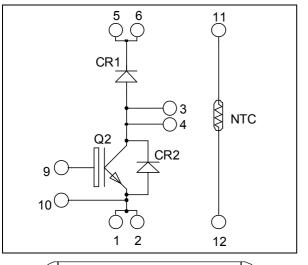
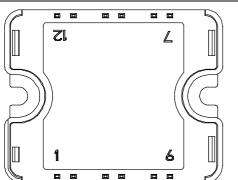


Boost chopper NPT IGBT Power Module

$V_{CES} = 1200V$ $I_{C} = 100 A^{*}$ (a) $T_{C} = 80^{\circ}C$





Pins 1/2; 3/4; 5/6 must be shorted together

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Non Punch Through (NPT) Fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- **RoHS** Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	130*	
I _C		$T_C = 80^{\circ}C$	100*	Α
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	200	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	735	W
RBSOA	Reverse Bias Safe Operating Area	$T_{\rm J} = 150^{\circ}{\rm C}$	200A @ 1150V	

Specification of IGBT device but output current must be limited to 75A to not exceed a delta of temperature greater than 30°C for the connectors.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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Тур

3.2

3.9

5.5

Max

250

3.7

6.5

600

Unit

μΑ

V

V

nA

All ratings (a) $T_i = 25^{\circ}C$ unless otherwise specified

 $V_{GE} = 20V, V_{CE} = 0V$

Electrical Characteristics Symbol Characteristic **Test Conditions** Min Zero Gate Voltage Collector Current $V_{GE} = 0V, V_{CE} = 1200V$ I_{CES} $V_{GE} = 15V$ $T_i = 25^{\circ}C$ $V_{CE(\text{sat})}$ Collector Emitter Saturation Voltage $I_{\rm C} = 100 {\rm A}$ $T_j = 125^{\circ}C$ $V_{GE} = V_{CE}$, $I_C = 4mA$ V_{GE(th)} 4.5

Dynamic Characteristics

IGES

Gate Threshold Voltage

Gate - Emitter Leakage Current

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		6.5		
C _{oes}	Output Capacitance	$V_{CE} = 25V$		1		nF
Cres	Reverse Transfer Capacitance	f = 1 MHz		0.5		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)		120		
T _r	Rise Time	$V_{GE} = \pm 15V$		50		ns
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 100A$		310		
T _f	Fall Time	$R_G = 5.6\Omega$		20		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C)		130		
T _r	Rise Time	$V_{GE} = \pm 15V$		60]
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 100A$		360		ns
$T_{\rm f}$	Fall Time	$R_G = 5.6\Omega$		30		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $T_j = 125^{\circ}C$		12		T.
E _{off}	Turn-off Switching Energy	$\begin{array}{c} I_{C} = 100 A \\ R_{G} = 5.6 \Omega \end{array} \qquad T_{j} = 125^{\circ} C \end{array}$		5		mJ

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$			100	μA
			$T_j = 125^{\circ}C$		100	500	
I _F	DC Forward Current		$Tc = 90^{\circ}C$		100		A
	Diode Forward Voltage	$I_{\rm F} = 100 {\rm A}$			2.4	3	
V _F		$I_{\rm F} = 150 {\rm A}$			2.7		V
		$I_{\rm F} = 100 {\rm A}$	$T_j = 125^{\circ}C$		1.8		
t _{rr}	Reverse Recovery Time	$I_{\rm p} = 100 \Delta$	$T_j = 25^{\circ}C$		385		ns
чп			$T_{j} = 125^{\circ}C$		480		
Q _{rr}	Reverse Recovery Charge	$di/dt = 200 A/\mu s$	$T_j = 25^{\circ}C$		1055		nC
Vrr			$T_{j} = 125^{\circ}C$		5240		ne

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Thermal and package characteristics

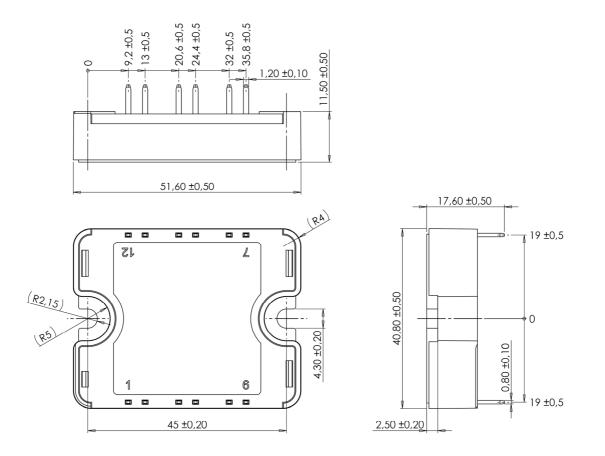
Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance		IGBT			0.19	°C/W
			Diode			0.55	C/ W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature					100	
Torque	Mounting torque	To heatsin	k M4	2		3	N.m
Wt	Package Weight				80	g	

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		Κ

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP1 Package outline (dimensions in mm)



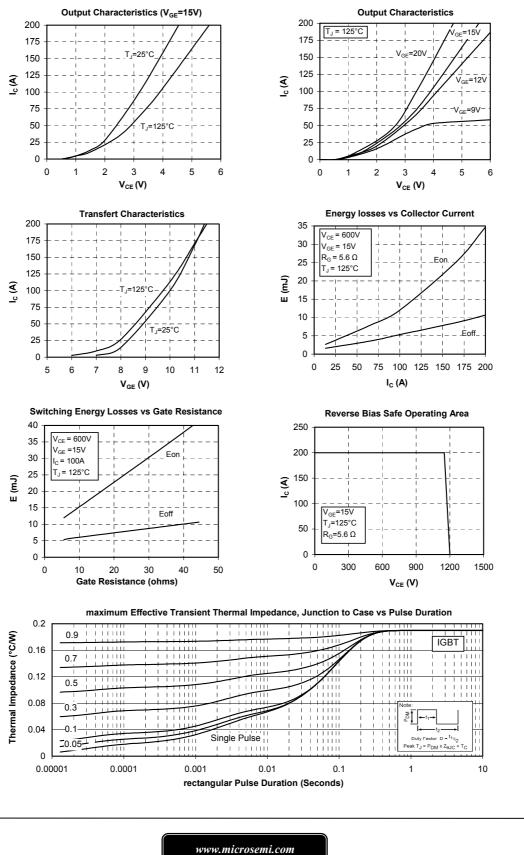
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

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Typical Performance Curve

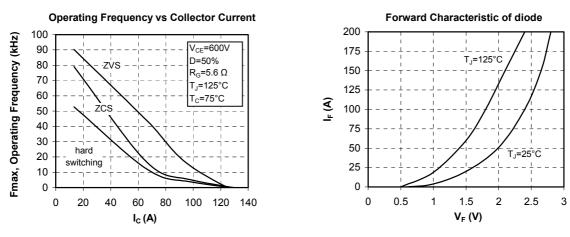


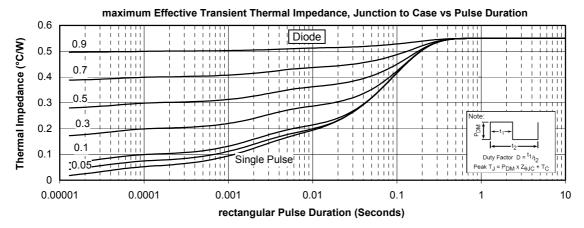
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